

**81CXXX/81NXXX****CMOS IC****VOLTAGE DETECTORS WITH
BUILT-IN DELAY TIME****DESCRIPTION**

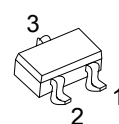
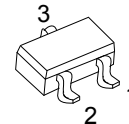
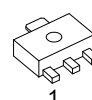
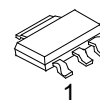
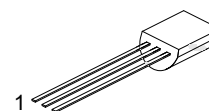
The UTC **81CXXX** and **81NXXX** series are good performance voltage detector and manufactured by CMOS technologies with highly accurate, low power consumption. A delay circuit is built-in to each detector, therefore, peripherals are unnecessary and high density mounting is possible. Detect voltage is extremely accurate with minimal temperature drift. Both CMOS and N-channel open drain output configurations are available.

FEATURES

- * Highly Accurate: Detect voltage $\pm 2\%$
- * Built-In Delay time : 1ms ~ 50ms
50ms ~ 200ms
200ms ~ 400ms
- * Detect Voltage Temperature Characteristics: TYP $\pm 100\text{ppm}/^\circ\text{C}$
- * Wide Operating Voltage Range : 0.7V ~ 10.0V
- * Low Current Consumption : TYP 1.0 μA ($V_{\text{IN}}=2.0\text{V}$)

ORDERING INFORMATION**CMOS:**

Ordering Number		①:Delay Time		Package	Pin Assignment			Packing
Lead Free	Halogen Free	Duration	Code		1	2	3	
81CxxL-①-AA3-B-R	81CxxG-①-AA3-B-R	1~50 ms 50~200 ms 200~400 ms	P Q R	SOT-223	O	G	I	Tape Reel
81CxxL-①-AB3-E-R	81CxxG-①-AB3-E-R			SOT-89	O	I	G	Tape Reel
81CxxL-①-AE3-3-R	81CxxG-①-AE3-3-R			SOT-23	O	G	I	Tape Reel
81CxxL-①-AE3-5-R	81CxxG-①-AE3-5-R			SOT-23	G	O	I	Tape Reel
81CxxL-①-AE3-2-R	81CxxG-①-AE3-2-R			SOT-23	I	O	G	Tape Reel
81CxxL-①-AE2-3-R	81CxxG-①-AE2-3-R			SOT-23-3	O	G	I	Tape Reel
81CxxL-①-AE2-5-R	81CxxG-①-AE2-5-R			SOT-23-3	G	O	I	Tape Reel
81CxxL-①-AE2-2-R	81CxxG-①-AE2-2-R			SOT-23-3	I	O	G	Tape Reel
81CxxL-①-T92-D-B	81CxxG-①-T92-D-B			TO-92	I	G	O	Tape Box
81CxxL-①-T92-E-B	81CxxG-①-T92-E-B			TO-92	O	I	G	Tape Box
81CxxL-①-T92-D-K	81CxxG-①-T92-D-K			TO-92	I	G	O	Bulk
81CxxL-①-T92-E-K	81CxxG-①-T92-E-K			TO-92	O	I	G	Bulk

**SOT-23-3**
(JEDEC TO-236)**SOT-23****SOT-89****SOT-223****TO-92**

■ ORDERING INFORMATION(Cont.)

N-Channel:

Ordering Number		①:Delay Time		Package	Pin Assignment			Packing
Lead Free	Halogen Free	Duration	Code		1	2	3	
81NxxL-①-AA3-B-R	81NxxG-①-AA3-B-R	1~50 ms 50~200 ms 200~400 ms	H J K	SOT-223	O	G	I	Tape Reel
81NxxL-①-AB3-E-R	81NxxG-①-AB3-E-R			SOT-89	O	I	G	Tape Reel
81NxxL-①-AE3-3-R	81NxxG-①-AE3-3-R			SOT-23	O	G	I	Tape Reel
81NxxL-①-AE3-5-R	81NxxG-①-AE3-5-R			SOT-23	G	O	I	Tape Reel
81NxxL-①-AE3-2-R	81NxxG-①-AE3-2-R			SOT-23	I	O	G	Tape Reel
81NxxL-①-AE2-3-R	81NxxG-①-AE2-3-R			SOT-23-3	O	G	I	Tape Reel
81NxxL-①-AE2-5-R	81NxxG-①-AE2-5-R			SOT-23-3	G	O	I	Tape Reel
81NxxL-①-AE2-2-R	81NxxG-①-AE2-2-R			SOT-23-3	I	O	G	Tape Reel
81NxxL-①-T92-D-B	81NxxG-①-T92-D-B			TO-92	I	G	O	Tape Box
81NxxL-①-T92-E-B	81NxxG-①-T92-E-B			TO-92	O	I	G	Tape Box
81NxxL-①-T92-D-K	81NxxG-①-T92-D-K			TO-92	I	G	O	Bulk
81NxxL-①-T92-E-K	81NxxG-①-T92-E-K			TO-92	O	I	G	Bulk

Note: 1. Pin assignment: I:V_{IN} O:V_{OUT} G:V_{SS}

2. xx: Output Voltage, refer to Marking Information.

	(1) R: Tape Reel, B: Tape Box, K: Bulk
	(2) refer to Pin Assignment
	(3) AA3: SOT-223, AE2: SOT-23-3 AB3: SOT-89, AE3: SOT-23, T92: TO-92,
	(4) ①: refer to Delay Time
	(5) G: Halogen Free, L: Lead Free
	(6) xx: refer to Marking Information
	(7) C: CMOS, N: N-Channel

MARKING INFORMATION

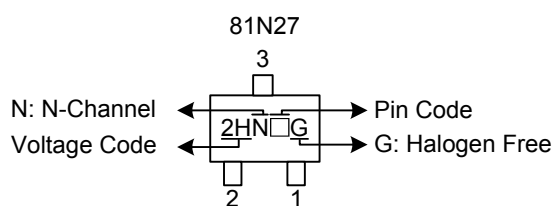
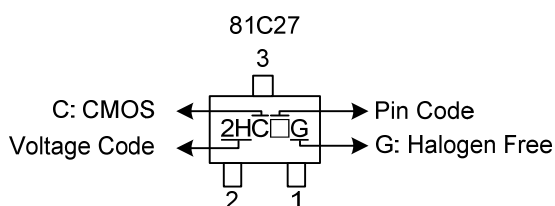
PACKAGE	VOLTAGE CODE			MARKING
SOT-223	10:1.0V	26:2.6V	42:4.2V 43:4.3V 44:4.4V 45:4.5V 46:4.6V 47:4.7V 48:4.8V 49:4.9V 50:5.0V	
	11:1.1V	27:2.7V		
	12:1.2V	28:2.8V		
	13:1.3V	29:2.9V		
	14:1.4V	30:3.0V		
SOT-89	15:1.5V	31:3.1V		
	16:1.6V	32:3.2V		
	17:1.7V	33:3.3V		
	18:1.8V	34:3.4V		
	19:1.9V	35:3.5V		
TO-92	20:2.0V	36:3.6V		
	21:2.1V	37:3.7V		
	22:2.2V	38:3.8V		
	23:2.3V	39:3.9V		
	24:2.4V	40:4.0V		
	25:2.5V	41:4.1V		

PACKAGE	INTEGER*	CODE	DECIMAL**	CODE	MARKING
SOT-23 SOT-23-3	1.	1	.0	A	
	2.	2	.1	B	
	3.	3	.2	C	
	4.	4	.3	D	
	5.	5	.4	E	
	6.	6	.5	F	
			.6	G	
			.7	H	
			.8	J	
			.9	K	

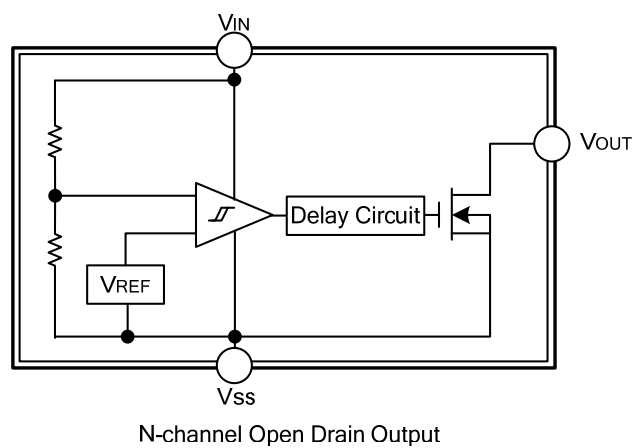
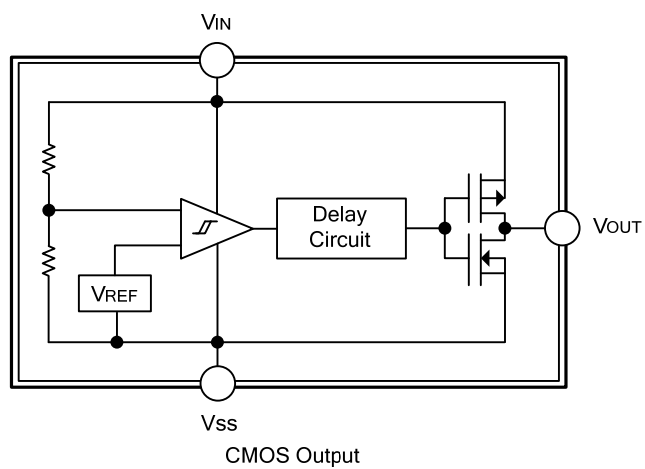
* Represents the integer of the Detect Voltage

** Represents the decimal number of the Detect Voltage

EXAMPLE:



■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Input Voltage		V_{IN}	12	V
Output Current		I_{OUT}	50	mA
Output Voltage	CMOS	V_{OUT}	$V_{SS}-0.3 \sim V_{IN}+0.3$	V
	N-Ch open drain		$V_{SS}-0.3 \sim 9$	V
Power Dissipation	SOT-223	P_D	800	mW
	SOT-23/ SOT-23-3		150	mW
	SOT-89		500	mW
	TO-92		300	mW
Operating Temperature		T_{OPR}	-30 ~ +80	°C
Storage Temperature		T_{STG}	-40 ~ +125	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Case	SOT-223	θ_{JC}	20	°C/W
	SOT-23/ SOT-23-3		200	°C/W
	SOT-89		45	°C/W
	TO-92		100	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Detection voltage (1.0V ~ 1.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF}(T) \times 0.98$	$V_{DF}(T)$	$V_{DF}(T) \times 1.02$	V
Hysteresis Range	V_{HYS}	1		$V_{DF} \times 0.02$	$V_{DF} \times 0.05$	$V_{DF} \times 0.08$	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=1.5V$		0.9	2.6	μA
			$V_{IN}=5.0$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=1.0V$		2.2		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				±100		ppm/°C
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

■ ELECTRICAL CHARACTERISTICS(Cont.)

Detection voltage (2.0V ~ 2.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF}(T) \times 0.98$	$V_{DF}(T)$	$V_{DF}(T) \times 1.02$	V
Hysteresis Range	V_{HYS}	1		$V_{DF} \times 0.02$	$V_{DF} \times 0.05$	$V_{DF} \times 0.08$	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=2.0V$		1.0	3.0	μA
			$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=2.0V$		7.9		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

Detection voltage (3.0V ~ 3.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF}(T) \times 0.98$	$V_{DF}(T)$	$V_{DF}(T) \times 1.02$	V
Hysteresis Range	V_{HYS}	1		$V_{DF} \times 0.02$	$V_{DF} \times 0.05$	$V_{DF} \times 0.08$	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=3.0V$		1.3	3.4	μA
			$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=3.0V$		10.1		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

■ ELECTRICAL CHARACTERISTICS(Cont.)

Detection voltage (4.0V ~ 4.9V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF}(T) \times 0.98$	$V_{DF}(T)$	$V_{DF}(T) \times 1.02$	V
Hysteresis Range	V_{HYS}	1		$V_{DF} \times 0.02$	$V_{DF} \times 0.05$	$V_{DF} \times 0.08$	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=4.0V$		1.5	3.8	μA
			$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=4.0V$		11.5		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

Detection voltage (5.0V)

PARAMETER	SYMBOL	CIRCUIT	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Detect Voltage	V_{DF}	1		$V_{DF}(T) \times 0.98$	$V_{DF}(T)$	$V_{DF}(T) \times 1.02$	V
Hysteresis Range	V_{HYS}	1		$V_{DF} \times 0.02$	$V_{DF} \times 0.05$	$V_{DF} \times 0.08$	V
Operating Voltage	V_{IN}	1	$V_{DF}=1.6V \sim 6.0V$	0.7		10.0	V
Supply Current	I_{SS}	2	$V_{IN}=5.0V$		2.0	4.2	μA
Output Current	I_{OUT}	3	N-ch $V_{DS}=0.5V, V_{IN}=5.0V$		13.0		mA
		4	P-ch $V_{DS}=2.1V, V_{IN}=8.0V$ (CMOS output)		-15.4		mA
V_{DF} Temperature Characteristics	$\frac{\Delta V_{DF}}{\Delta T_{OPR} \times V_{DF}}$				± 100		ppm/ $^{\circ}C$
Transient Delay Time ($V_{DR} \rightarrow V_{OUT}$ inversion)	t_{DLY}^*	5	V_{IN} changes from 0.6V ~ 10V	50		200	ms

$V_{DF}(T)$: established detect voltage value

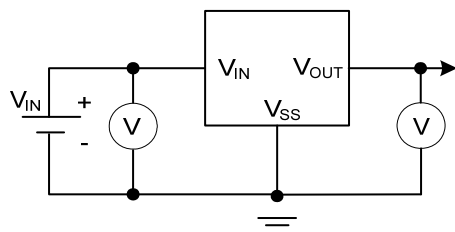
Release Voltage: $V_{DR} = V_{DF} + V_{HYS}$

* Transient Delay Time: 1ms ~ 50ms & 200ms ~ 400ms versions are also available.

Note: The power consumption during power-start to output being stable (release operation) is 2 μA greater than it is after that period (completion of release operation) because of delay circuit through current.

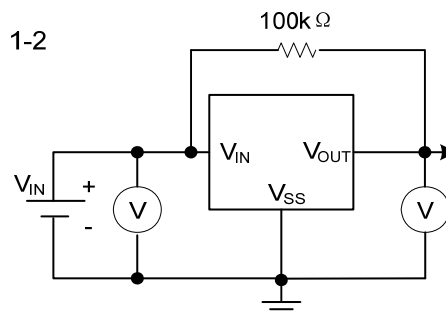
■ TEST CIRCUITS

1-1



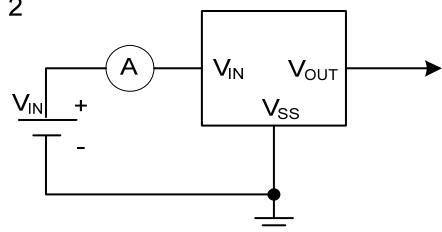
Cmos Output

1-2

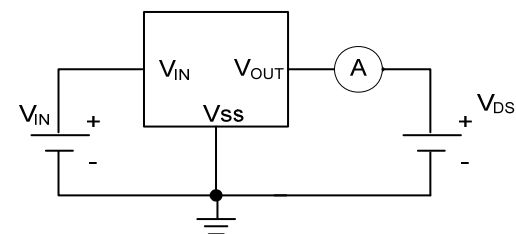


N-channel Open Drain Output

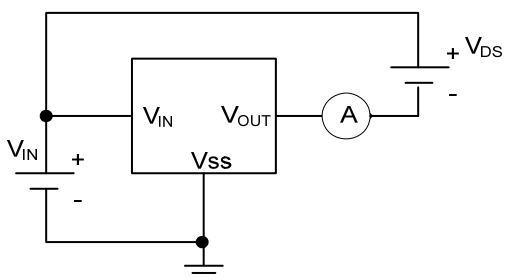
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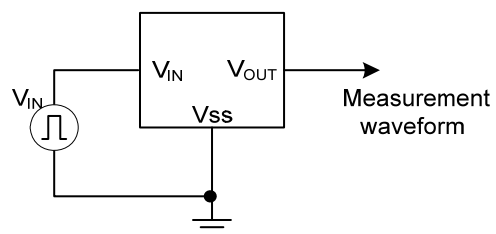
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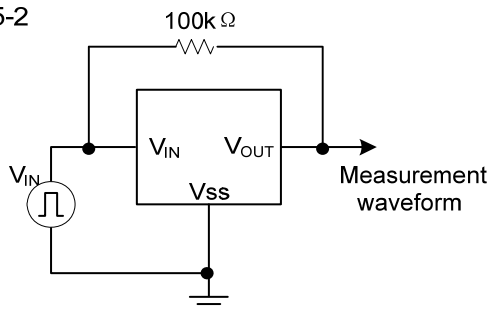


5-1



Cmos Output

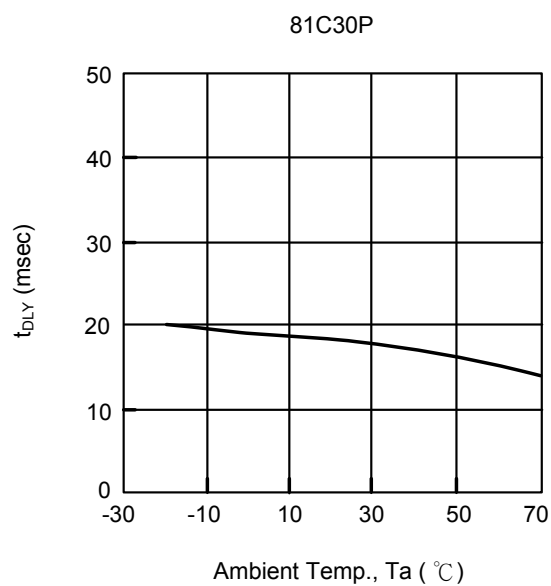
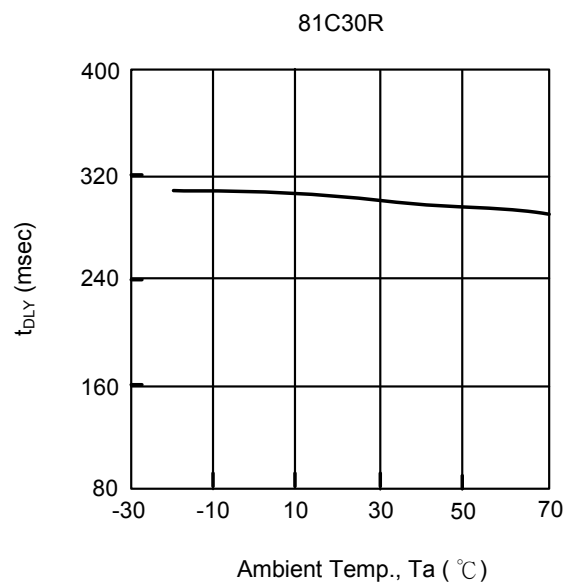
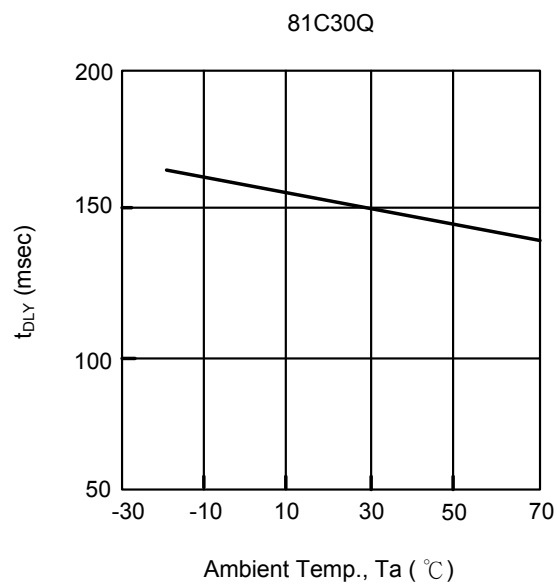
5-2



N-channel Open Drain Output

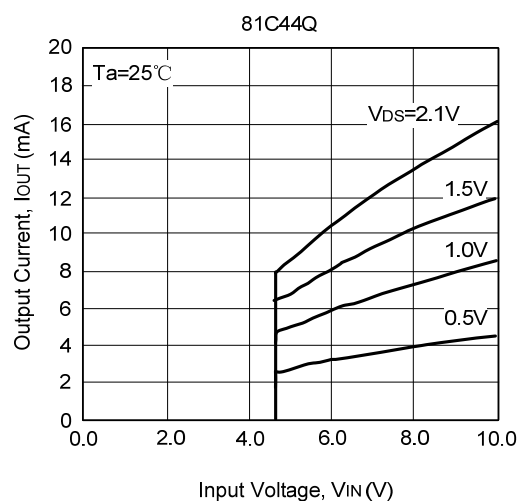
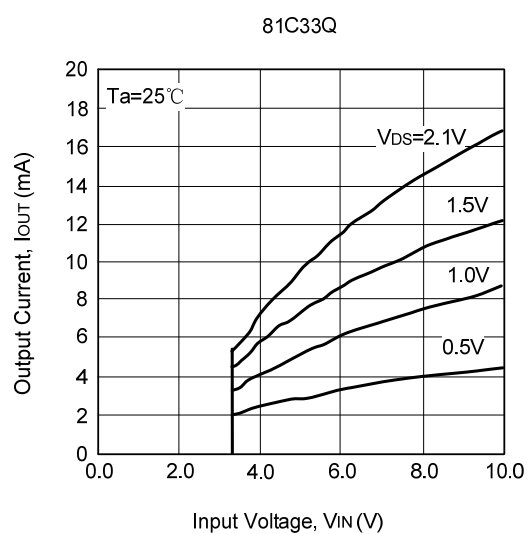
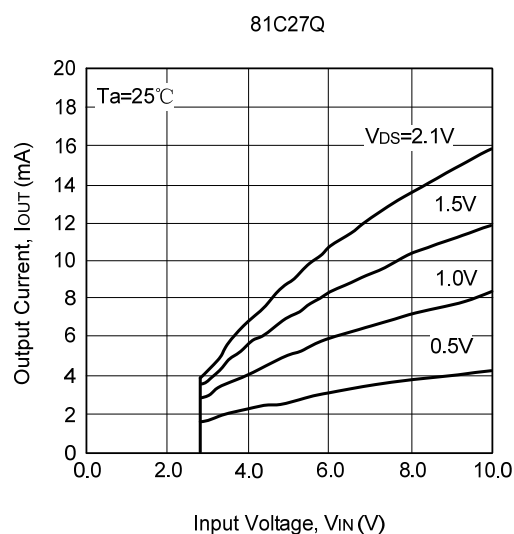
■ TYPICAL PERFORMANCE CHARACTERISTICS

(1) AMBIENT TEMPERATURE vs. TRANSIENT DELAY TIME

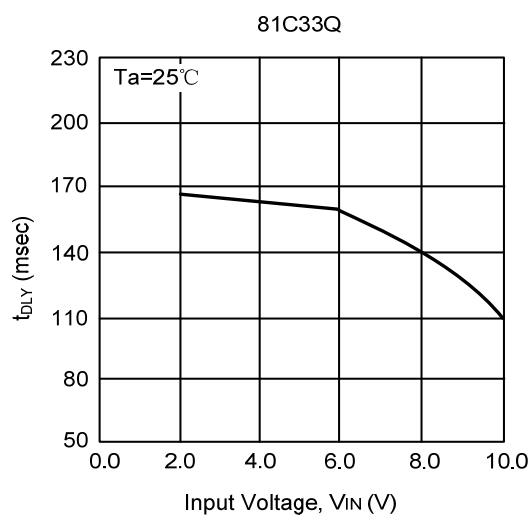


■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)

(2) P-CHANNEL DRIVER OUTPUT CURRENT vs. INPUT VOLTAGE

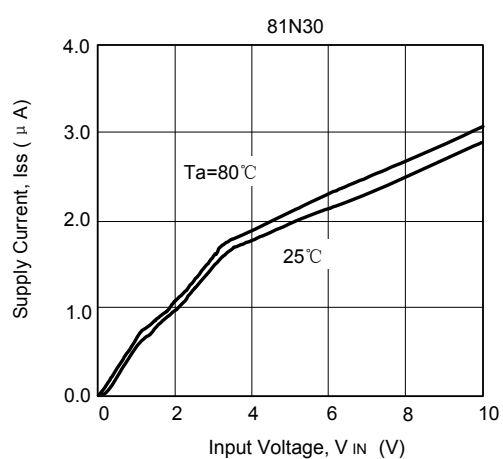
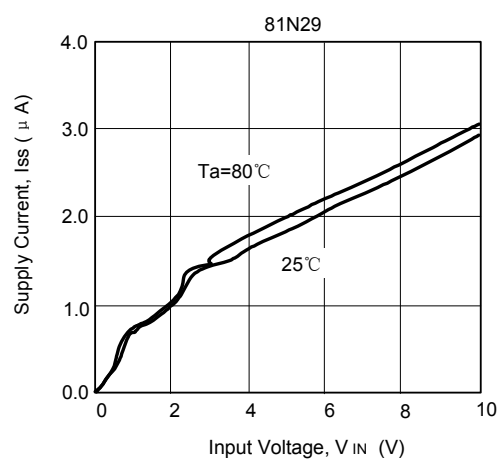
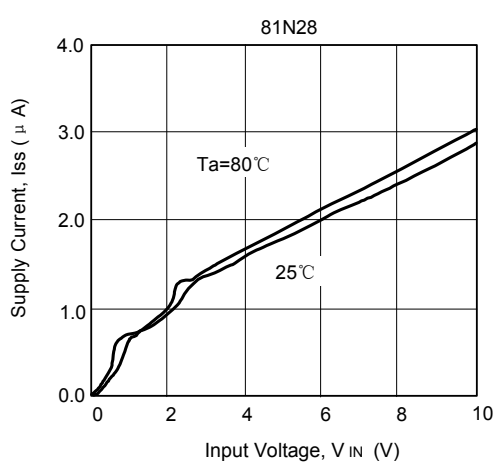
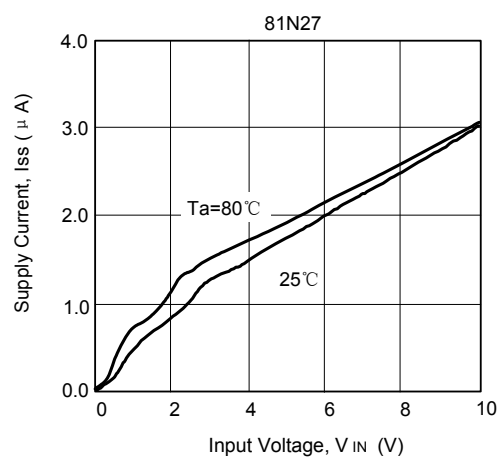
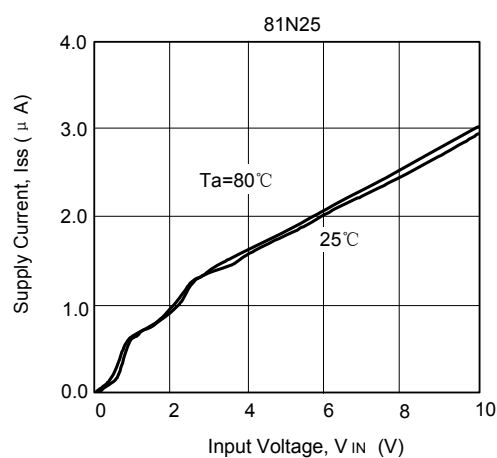
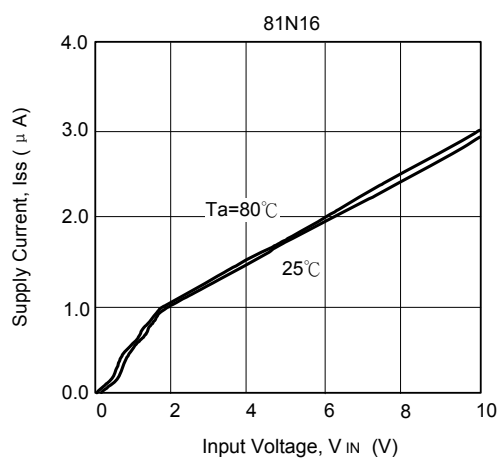


(2) TRANSIENT DELAY TIME vs. INPUT VOLTAGE

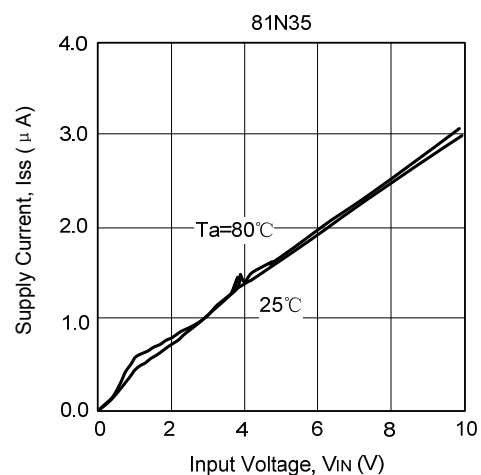
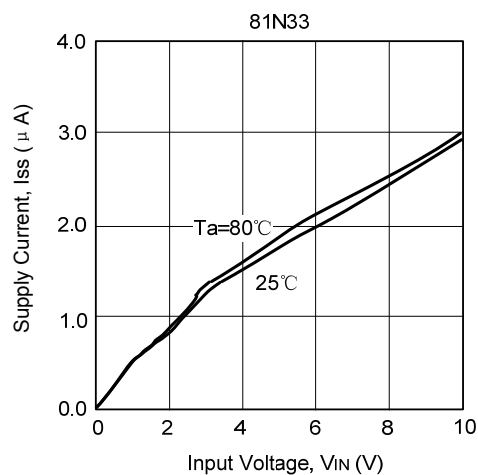


TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)

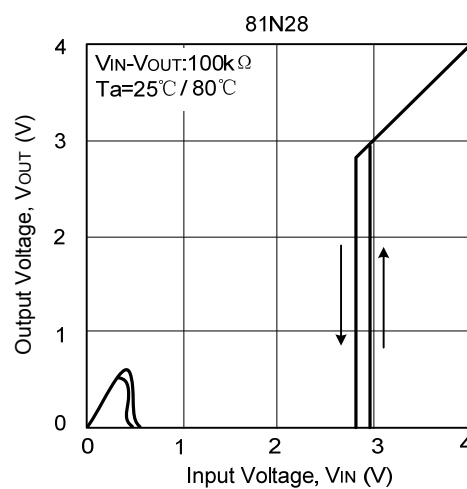
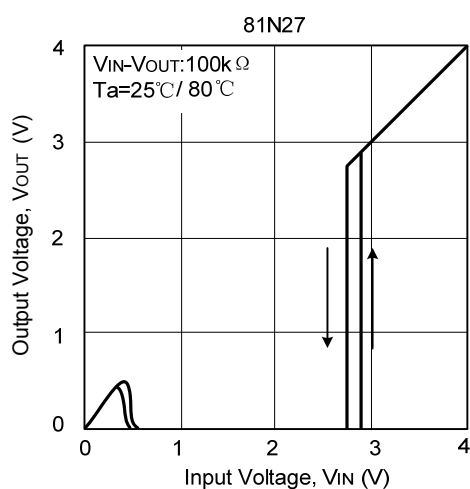
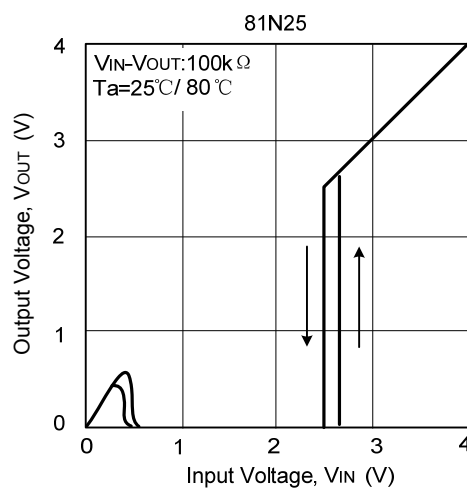
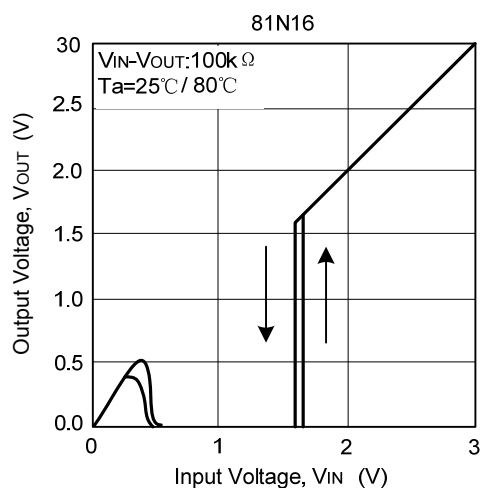
(3) SUPPLY CURRENT vs. INPUT VOLTAGE



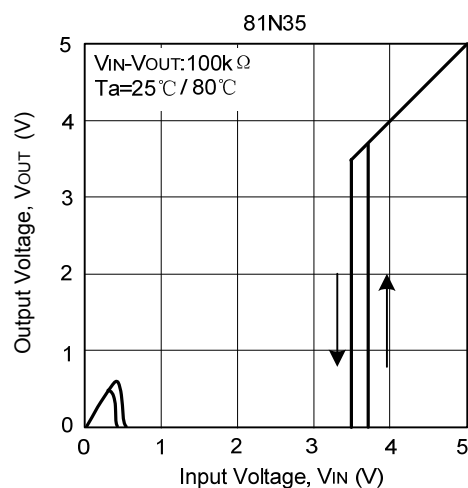
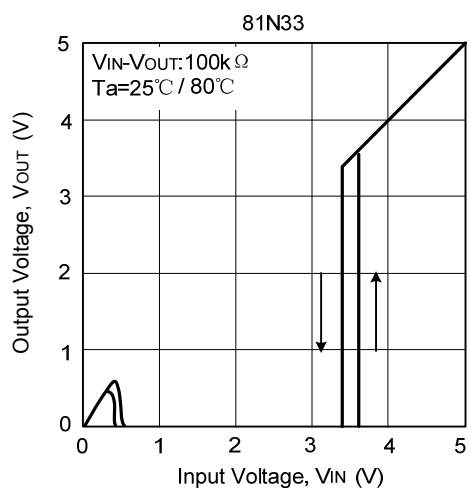
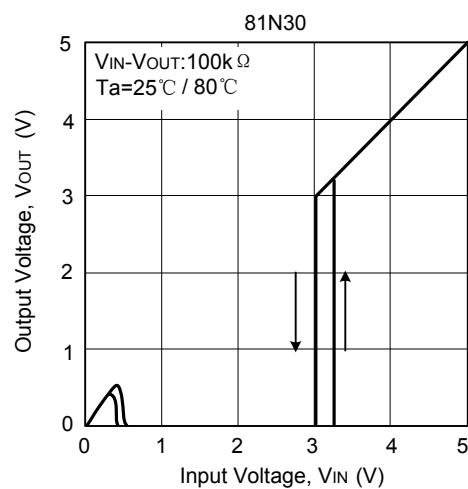
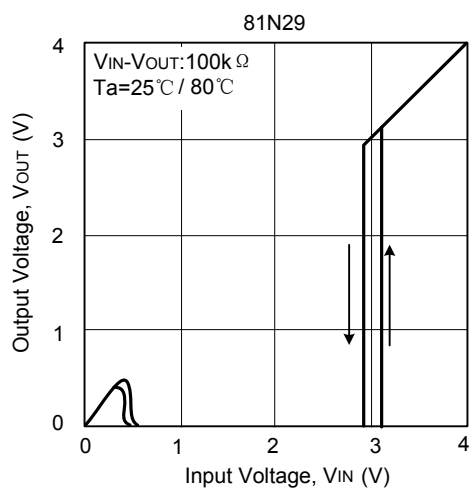
■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



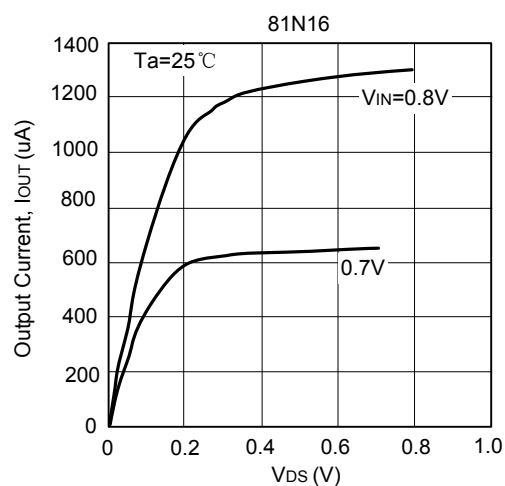
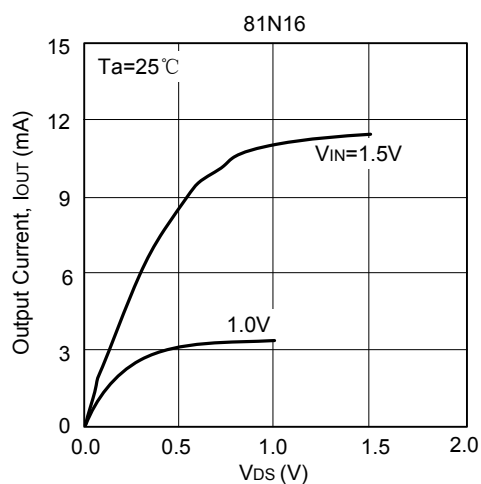
(4) OUTPUT VOLTAGE vs. INPUT VOLTAGE



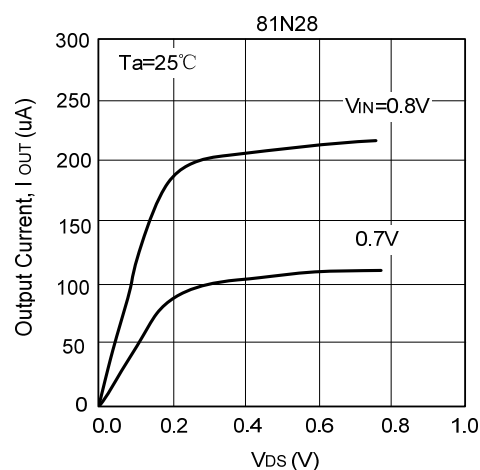
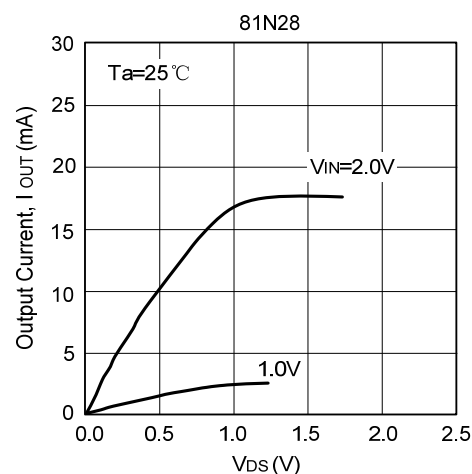
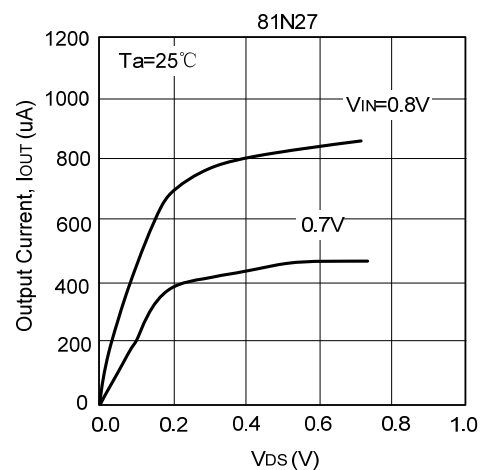
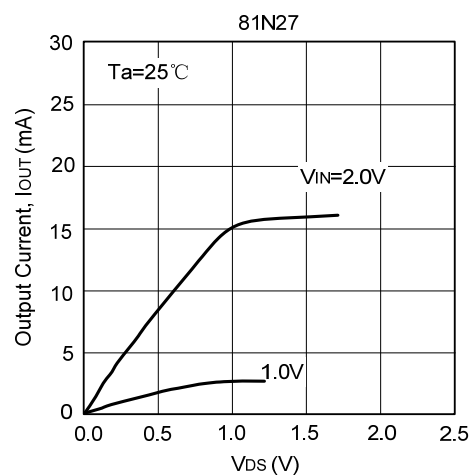
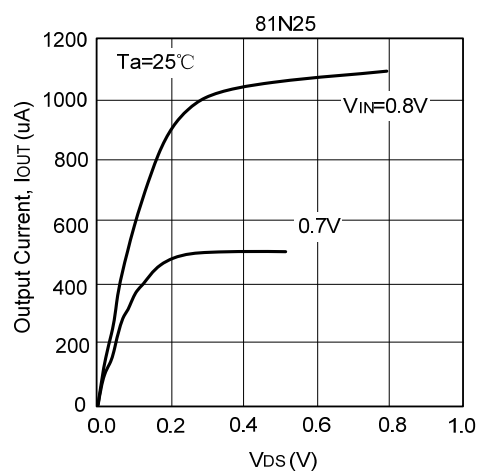
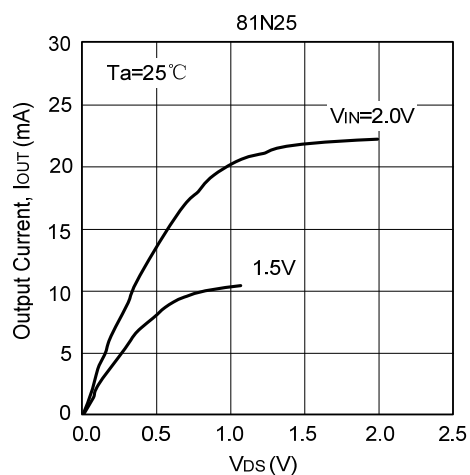
■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



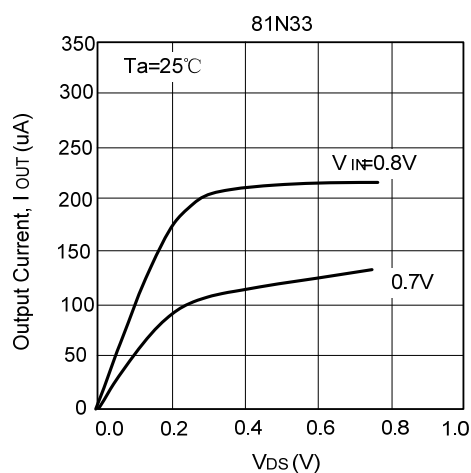
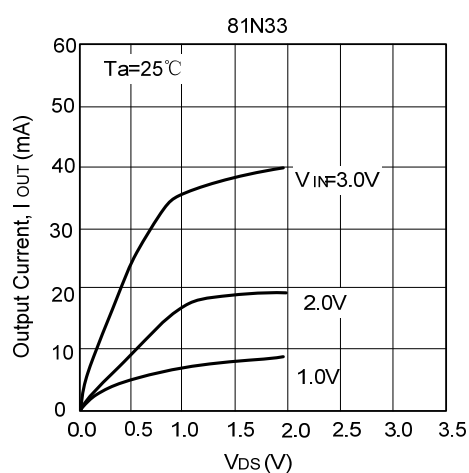
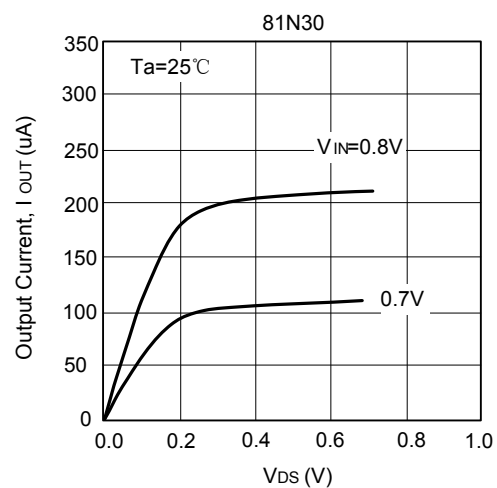
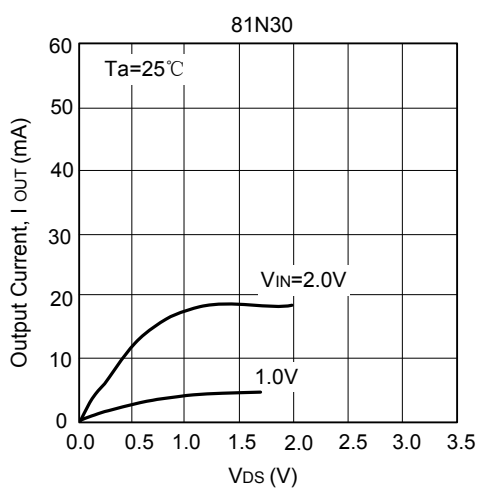
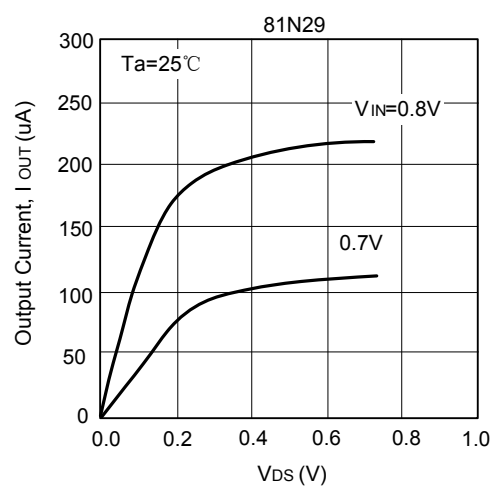
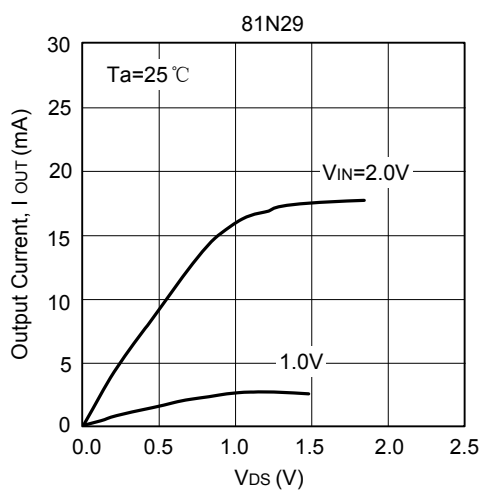
(5) N-CHANNEL DRIVE OUTPUT CURRENT vs. V_{DS}



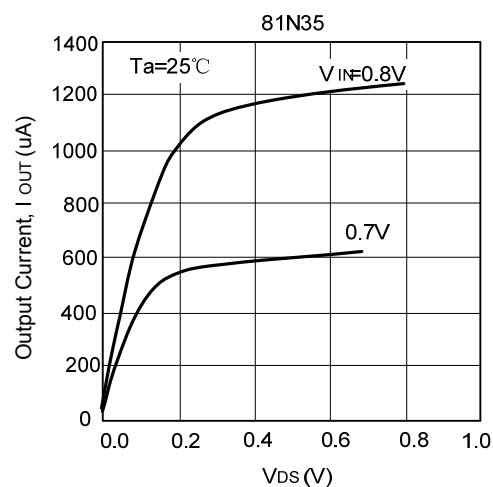
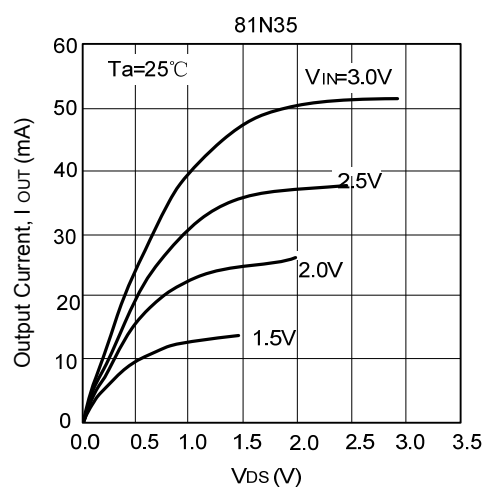
■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



■ TYPICAL PERFORMANCE CHARACTERISTICS(Cont.)



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